



Dual N-channel 20V, TSSOP-8 MOSFET 双 N-溝道場效應管

■ Features 特點

Low on-resistance and maximum DC current capability 低導通電阻和最大直流電流能力

Super high density cell design 超高元胞密度設計

$R_{DS(ON)} \leq 20m\Omega @ V_{GS}=4.5V$

$R_{DS(ON)} \leq 23m\Omega @ V_{GS}=2.5V$

■ Applications 應用

Power Management in Note book 筆記本電源管理

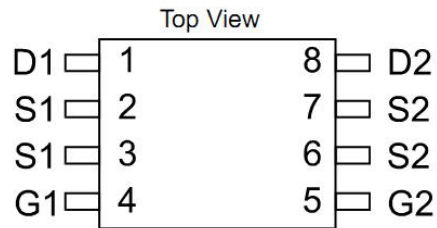
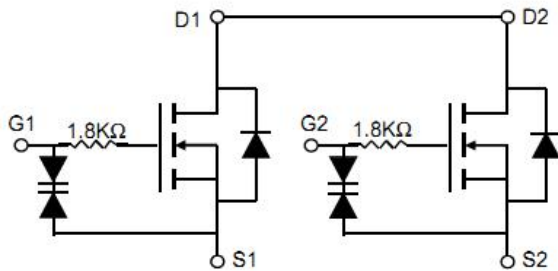
Portable Equipment 便攜式設備

Battery Powered System 電池電源系統

DC/DC Converter 直流/直流變換

Load Switch 負載開關應用

■ Internal Schematic Diagram 內部結構



■ Absolute Maximum Ratings 最大額定值

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	20	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	±8	V
Drain Current (continuous)漏極電流-連續	I_D	7	A
Drain Current (pulsed)漏極電流-脈沖	I_{DM}	25	A
Total Device Dissipation 總耗散功率	$P_{TOT}(at TC = 25^{\circ}C)$ $(at TC = 70^{\circ}C)$	1.5 1	W
Thermal Resistance Junction-Ambient 熱阻	$R_{\theta JA}$	83	$^{\circ}C/W$
Junction/Storage Temperature 結溫/儲存溫度	T_J, T_{stg}	-55~150	$^{\circ}C$



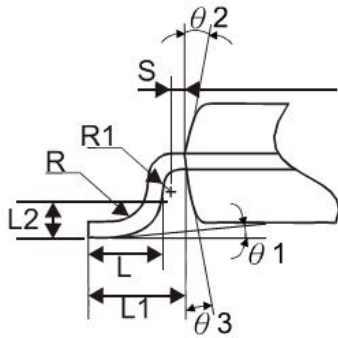
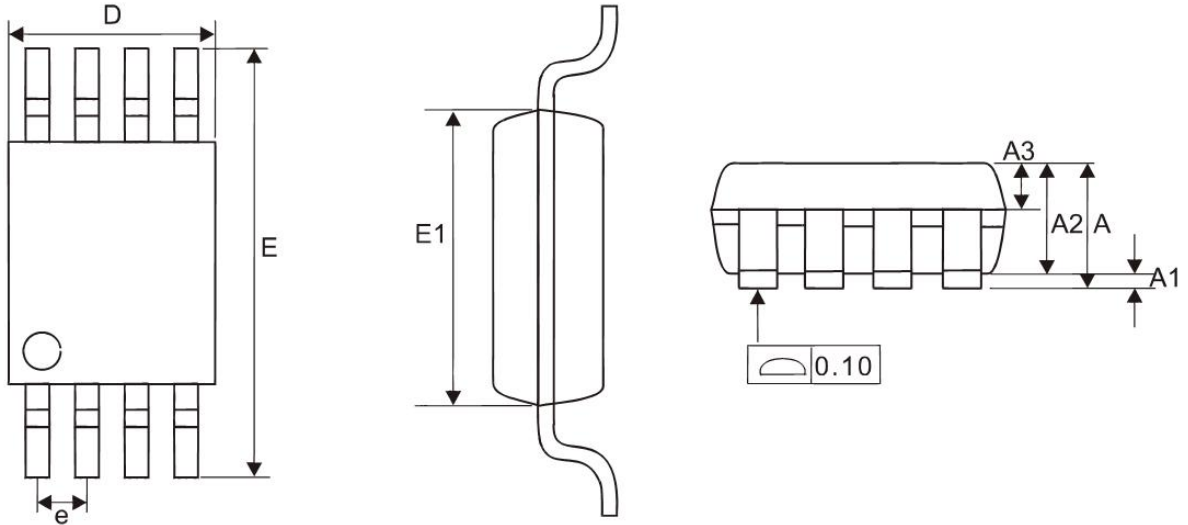
■ Electrical Characteristics 電特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓($I_D=250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	20	—	—	V
Gate Threshold Voltage 柵極開啓電壓($I_D=250\mu\text{A}, V_{GS}=V_{DS}$)	$V_{GS(th)}$	0.4	—	1.1	V
Zero Gate Voltage Drain Current 零柵壓漏極電流($V_{GS}=0\text{V}, V_{DS}=20\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 柵極漏電流($V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 10	μA
Static Drain-Source On-State Resistance 靜態漏源導通電阻($I_D=7\text{A}, V_{GS}=4.5\text{V}$) ($I_D=6.5\text{A}, V_{GS}=2.5\text{V}$)	$R_{DS(ON)}$	—	16 18	20 23	$\text{m}\Omega$
Diode Forward Voltage Drop 內附二極管正向壓降($I_{SD}=1\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	1	V
Input Capacitance 輸入電容 ($V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$)	C_{ISS}	—	1295	—	pF
Common Source Output Capacitance 共源輸出電容($V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$)	C_{OSS}	—	160	—	pF
Reverse Transfer Capacitance 反向傳輸電容 ($V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$)	C_{RSS}	—	87	—	pF
Gate Source Charge 柵源電荷密度 ($V_{DS}=10\text{V}, I_D=7\text{A}, V_{GS}=4.5\text{V}$)	Q_{gs}	—	4.2	—	nC
Gate Drain Charge 柵漏電荷密度 ($V_{DS}=10\text{V}, I_D=7\text{A}, V_{GS}=4.5\text{V}$)	Q_{gd}	—	2.6	—	nC
Turn-On Delay Time 開啓延遲時間 ($V_{DS}=10\text{V}, I_D=1\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	$t_{d(on)}$	—	280	—	ns
Turn-On Rise Time 開啓上升時間 ($V_{DS}=10\text{V}, I_D=1\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	t_r	—	328	—	ns
Turn-Off Delay Time 關斷延遲時間 ($V_{DS}=10\text{V}, I_D=1\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	$t_{d(off)}$	—	3760	—	ns
Turn-On Fall Time 開啓下降時間 ($V_{DS}=10\text{V}, I_D=1\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	t_f	—	2240	—	ns



■ DIMENSION 外形封裝尺寸



SYMBOL	MILLIMETERS	
	MIN	MAX
A	-	1.20
A1	0.05	0.15
A2	0.90	1.05
A3	0.34	0.54
D	2.90	3.10
E	6.20	6.60
E1	4.30	4.50
e	0.65BSC	
L	0.45	0.75
L1	1.00REF	
L2	0.25BSC	
R	0.09	-
R1	0.09	-
S	0.20	-
$\theta 1$	0°	8°
$\theta 2$	10°	14°
$\theta 3$	10°	14°

Note: 1. Refer to JEDEC MS-012AA.

2. Dimension "D" does not include mold flash, protrusions